

A1 N-Channel Enhancement Mode MOSFET ASM2306

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(ON)} (m) Max
20V	2.8A	45 @ V _{GS} = 4.5V
		60 @ V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- SOT-23 package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	± 8	V
Drain Current-Continuous ^a @ T _J =125°C -Pulsed ^b	I _D	2.8	A
	I _{DM}	12	A
Drain-Source Diode Forward Current ^a	I _S	1.25	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{thJA}	100	°C/W
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